

Features

- Ultra Low Capacitance 0.6pF
- Ipp Max=2A(@8/20us)
- Stand-off Voltage:5V

Applications

- USB-2.0
- High speed antenna applications

Item	Characteristics
Wafer size	6inch
Chip size	340 * 340 um
Top Metalization	Al-Si

Maximum Ratings (Ta=25degC)

Symbol	Parameter	Value	Units
Pd	Power Dissipation (*1)	150	mW
Tstg	Storage Temperature Range	-55 to+150	Deg C
Tj	Maximum junction temperature (*1)	-55 to+125	Deg C
Vpp	Electrostatic discharge		
	IEC61000-4-2 Air Discharge (*1)(*2)	±15	kV
	IEC61000-4-2 Contact Discharge (*1)	±10	kV

(*1) Rating value for reference on a SOT-23 package configuration (front: Au wire 35um, back: Au eutectic), mounted on PCB of 1.5cm by 2.5cm.

(*2) Reference only

Electrical Characteristics (Ta=25degC)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Condition
Reverse stand-off voltage	V _{RWM}	-	-	5.0	V	
Leakage current	I _R	-	-	1.0	uA	V _{RWM} = 5V
Breakdown voltage	V _{BR}	6.0	-	-	V	I = 1mA
Capacitance (*1)	C	-	0.6	0.9	pF	V _R = 0V, f = 1MHz
Clamping voltage (*1)	V _c	-	-	14	V	I _{pp} =1A (tp=8/20us)
I _{pp} Max	I _p	-	-	2	A	tp=8/20us

(*1) Package=SOT-23(front: Au wire 35um, back: Au eutectic)

Note
